

Product data sheet

### 1. General description

High voltage, high speed planar passivated NPN power switching transistor in a SOT78 (TO-220AB) plastic package.

### 2. Features and benefits

- Fast switching
- Low thermal resistance
- Very high voltage capability
- Very low switching and conduction losses

### 3. Applications

- DC-to-DC converters
- High frequency electronic lighting ballasts
- Inverters
- Motor control systems

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CM</sub>	peak collector current	Fig. 1; Fig. 2; Fig. 3		-	-	8	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; <u>Fig. 4</u>		-	-	80	W
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	-	1050	V
Static charac	teristics						
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 0.1 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; Fig. 11	[1]	48	66	100	
		I <sub>C</sub> = 0.8 A; V <sub>CE</sub> = 3 V; T <sub>mb</sub> = 25 °C; Fig. 12	[1]	25	42	50	

[1] Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  2 %

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# 5. Pinning information

Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	В	base	mb	C				
2	С	collector	$\downarrow \bigcirc \downarrow$	в				
3	E	emitter						
mb	C	mounting base; connected to collector		E sym123				
			TO-220AB (SOT78)					

# 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
BUJ302A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78				

BUJ302A

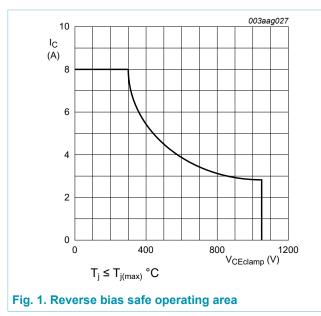
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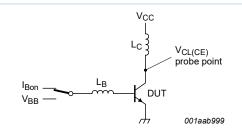
# 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V	-	1050	V
V <sub>CEO</sub>	collector-emitter voltage	I <sub>B</sub> = 0 A	-	400	V
V <sub>EBO</sub>	emitter-base voltage	I <sub>C</sub> = 0 A; I <sub>E</sub> = 2 A; t <sub>p</sub> < 10 ms	-	24	V
I <sub>C</sub>	collector current	Fig. 1; Fig. 2; Fig. 3	-	4	А
I <sub>CM</sub>	peak collector current		-	8	А
I <sub>B</sub>	base current		-	2	А
I <sub>BM</sub>	peak base current		-	4	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> ≤ 25 °C; <u>Fig. 4</u>	-	80	W
T <sub>stg</sub>	storage temperature		-65	150	°C
Tj	junction temperature		-	150	°C





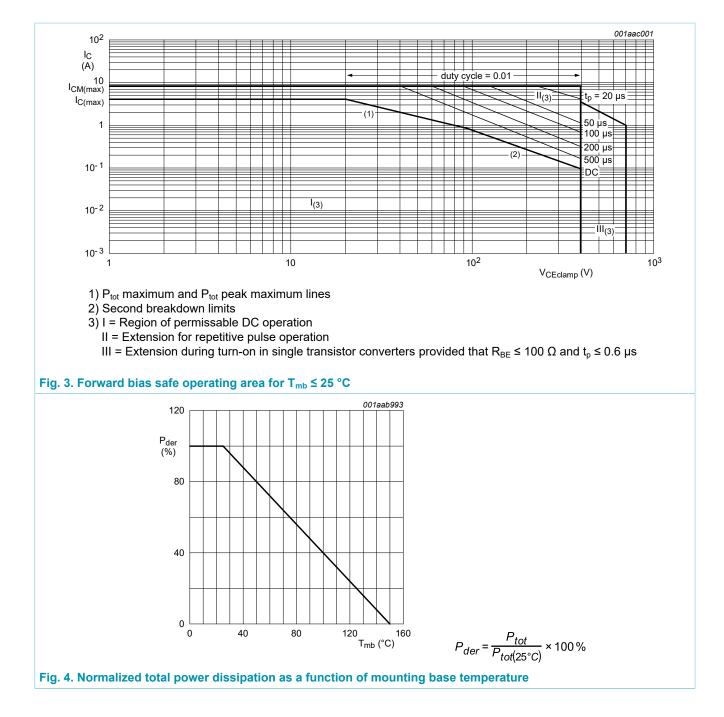
 $\begin{array}{l} V_{CL(CE)} \leq 1000 \; V; \; V_{CC} = 150 \; V; \; V_{BB} = - \; 5 \; V; \\ L_B = 1 \; \mu H; \; L_C = 200 \; \mu H \end{array}$ 

Fig. 2. Test circuit for reverse bias safe operating area

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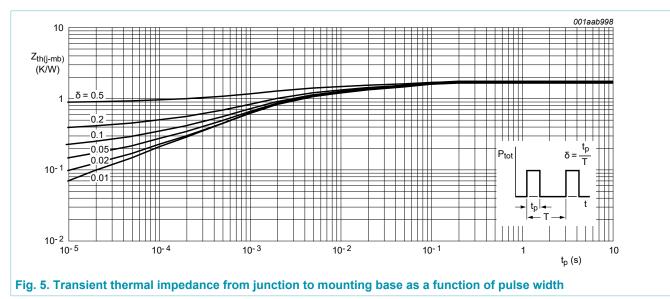
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### 8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	1.56	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W

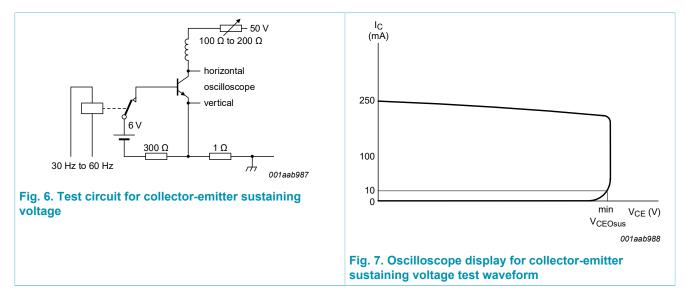


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#### 9. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	cteristics						
I <sub>CES</sub>	collector-emitter cut-off current (base shorted)	$V_{BE}$ = 0 V; $V_{CE}$ = 1050 V; $T_{mb}$ = 25 °C		-	0.2	10	μA
I <sub>CEO</sub>	collector-emitter cut-off current (base open)	$V_{CE}$ = 400 V; I <sub>B</sub> = 0 A; T <sub>mb</sub> = 25 °C		-	10	250	mA
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	I <sub>B</sub> = 1 mA; I <sub>C</sub> = 0 A; T <sub>mb</sub> = 25 °C		15	19	-	V
V <sub>CEOsus</sub>	collector-emitter sustaining voltage (base open)	I <sub>B</sub> = 0 A; I <sub>C</sub> = 10 mA; L <sub>C</sub> = 25 mH; T <sub>mb</sub> = 25 °C; <u>Fig. 6; Fig. 7</u>	[1]	400	470	-	V
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 0.2 A; T <sub>mb</sub> = 25 °C; <u>Fig. 8;</u> <u>Fig. 9</u>	[1]	-	0.15	0.5	V
		I <sub>C</sub> = 3.5 A; I <sub>B</sub> = 1 A; T <sub>mb</sub> = 25 °C; <u>Fig. 8;</u> <u>Fig. 9</u>	[1]	-	0.6	1.5	V
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 3.5 A; I <sub>B</sub> = 1 A; T <sub>mb</sub> = 25 °C; <u>Fig. 10</u>	[1]	-	1.1	1.5	V
h <sub>FE</sub>	DC current gain	I <sub>C</sub> = 0.1 A; V <sub>CE</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 11</u>	[1]	48	66	100	
		I <sub>C</sub> = 0.8 A; V <sub>CE</sub> = 3 V; T <sub>mb</sub> = 25 °C; <u>Fig. 12</u>	[1]	25	42	50	
Dynamic cha	aracteristics						
t <sub>s</sub>	storage time	I <sub>C</sub> = 2.5 A; I <sub>Bon</sub> = 0.5 A; I <sub>Boff</sub> = -0.5 A;		-	-	3.5	μs
t <sub>f</sub>	fall time	R <sub>L</sub> = 60 Ω; V <sub>BB</sub> = -5 V; T <sub>mb</sub> = 25 °C; resistive load; t <sub>p</sub> = 300 μs; <u>Fig. 13;</u> <u>Fig. 14</u>		-	-	500	ns

[1] Pulse test: pulse duration  $\leq$  300 µs, duty cycle  $\leq$  2 %



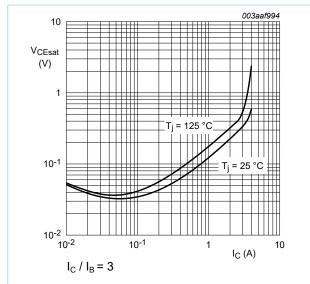
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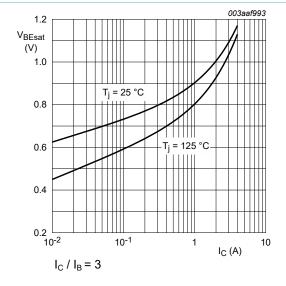
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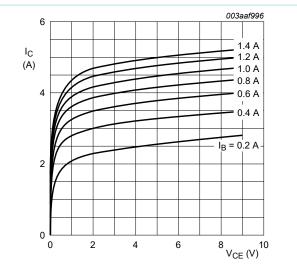
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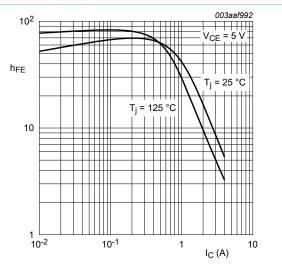
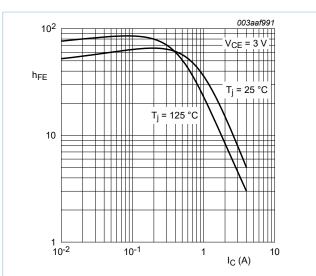


Fig. 11. DC current gain as a function of collector current; typical values

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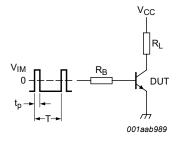
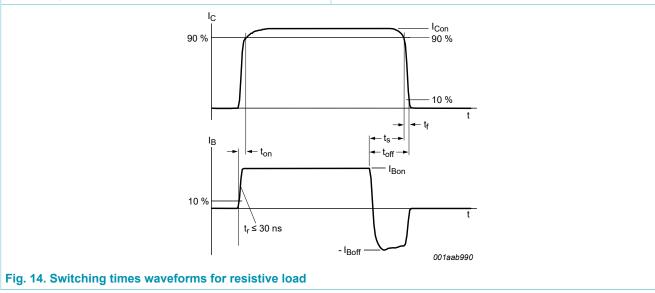
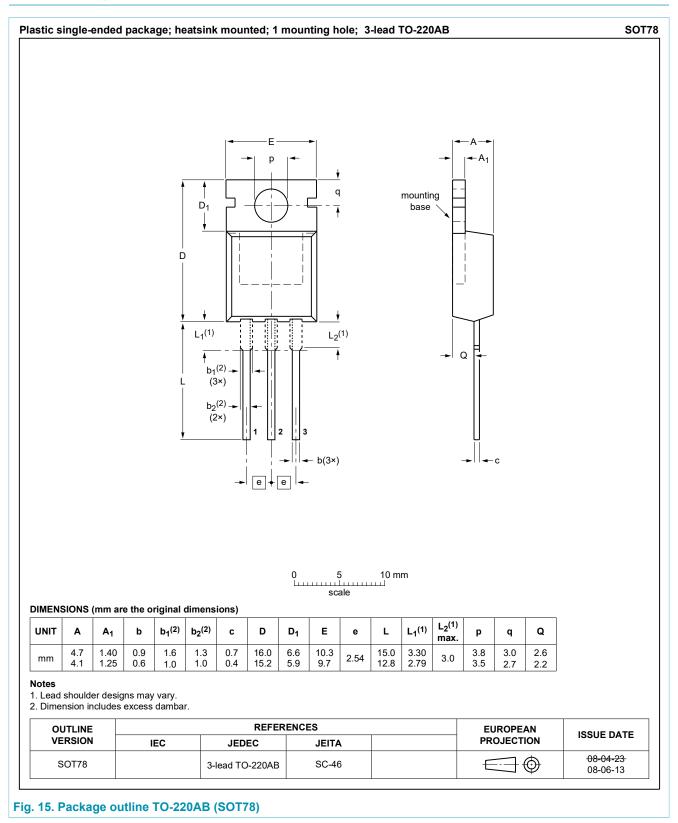


Fig. 13. Test circuit for resistive load switching





#### **10. Package outline**



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### 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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